

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

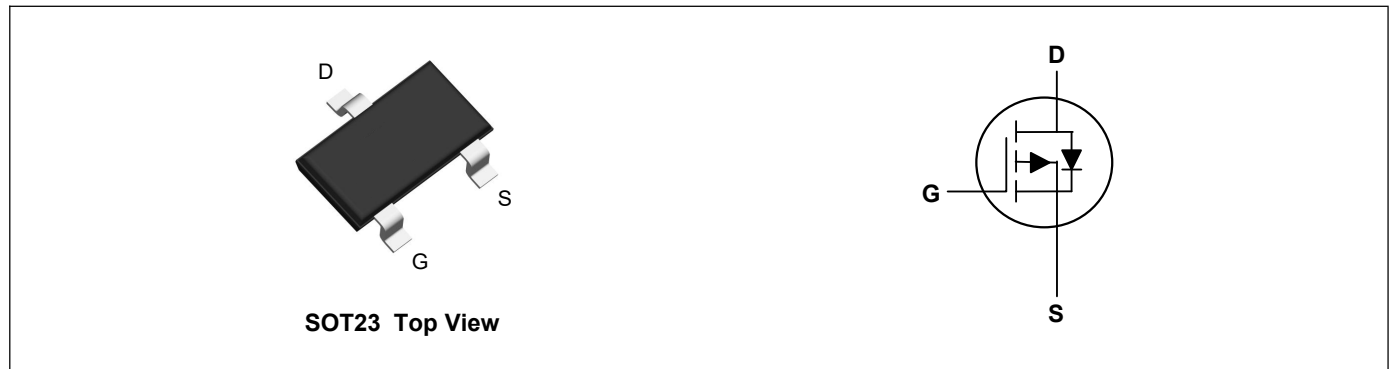
Product Summary



V_{DS}	-30	V
I_D	-4.2	A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	55	m Ω
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	75	m Ω

Applications

- High Frequency Point-of-Load, Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch



Absolute Maximum Ratings($T_A=25^{\circ}C$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ¹	$I_D@T_A=25^{\circ}C$	-4.2	A
Pulsed Drain Current ²	I_{DM}	-30	A
Total Power Dissipation	$P_D@T_A=25^{\circ}C$	1.4	W
Storage Temperature Range	T_{STG}	-55 to 150	$^{\circ}C$
Operating Junction Temperature Range	T_J	-55 to 150	$^{\circ}C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	---	104	$^{\circ}C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30	---	---	V
Static Drain-Source On-Resistance ²	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-4.2A$	---	48	55	m Ω
		$V_{GS}=-4.5V, I_D=-4A$	---	56	75	m Ω
		$V_{GS}=-2.5V, I_D=-1A$	---	72	90	m Ω
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-0.5	---	-1.3	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=-24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$	---	---	± 100	nA
Forward Transconductance	g_{fs}	$V_{DS}=-5V, I_D=-4.2A$	---	10	---	S
Total Gate Charge	Q_g	$V_{DS}=-15V, V_{GS}=-4.5V, I_D=-4.2A$	---	8.5	---	nC
Gate-Source Charge	Q_{gs}		---	1.8	---	
Gate-Drain Charge	Q_{gd}		---	2.7	---	
Turn-On Delay Time	$T_{d(on)}$	$V_{DD}=-15V, V_{GS}=-10V, I_D=-4.2A, R_G=6\Omega$	---	7	---	ns
Rise Time	T_r		---	3	---	
Turn-Off Delay Time	$T_{d(off)}$		---	30	---	
Fall Time	T_f		---	12	---	
Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V, f=1\text{MHz}$	---	880	---	pF
Output Capacitance	C_{oss}		---	105	---	
Reverse Transfer Capacitance	C_{rss}		---	65	---	

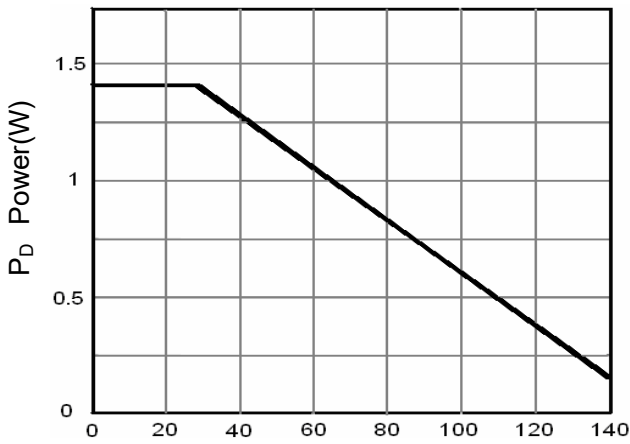
Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Diode Forward Voltage ²	V_{SD}	$V_{GS}=0V, I_S=-4.2A, T_J=25^\circ\text{C}$	---	---	-1.2	V

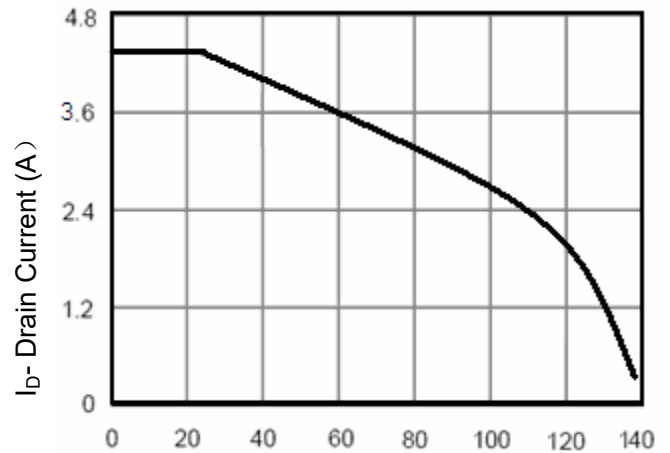
Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150 $^\circ\text{C}$ junction temperature

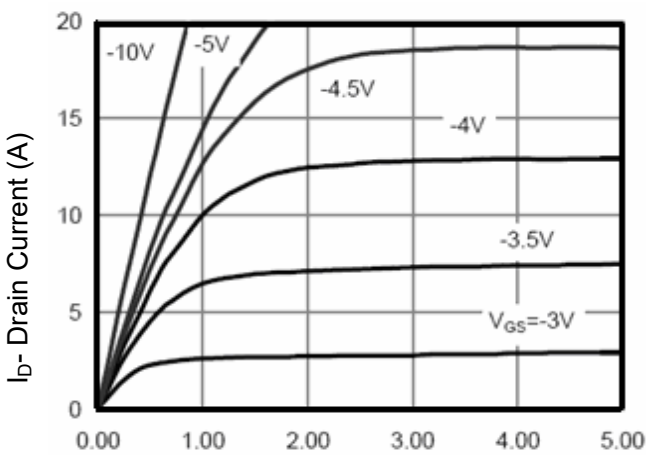
Typical Characteristics



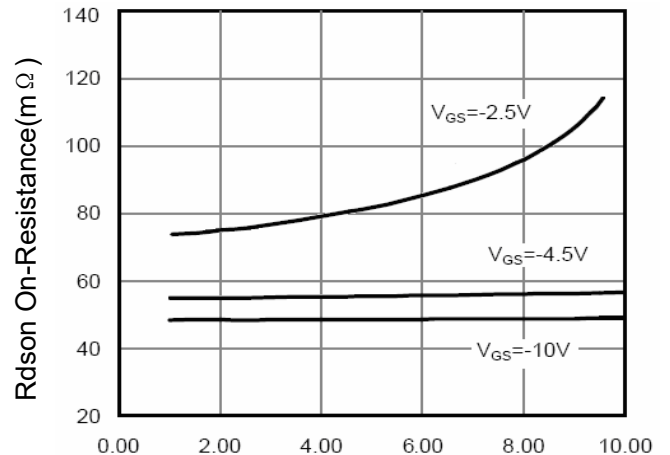
T_J-Junction Temperature(°C)
Figure 1 Power Dissipation



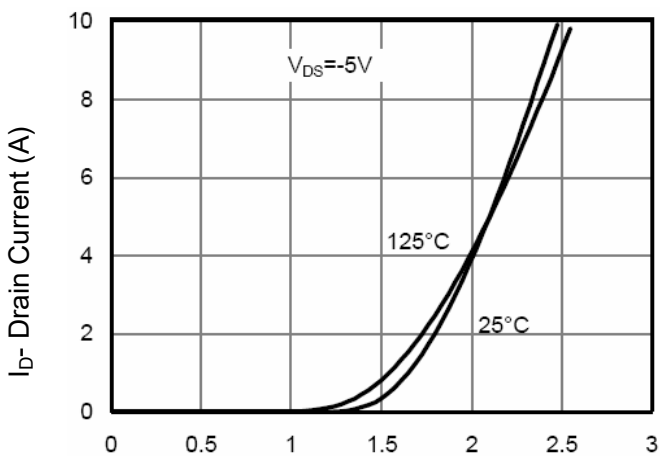
T_J-Junction Temperature(°C)
Figure 2 Drain Current



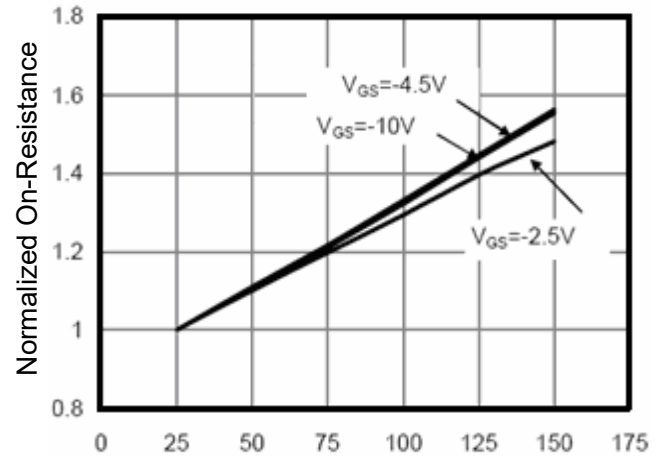
V_{ds} Drain-Source Voltage (V)
Figure 3 Output Characteristics



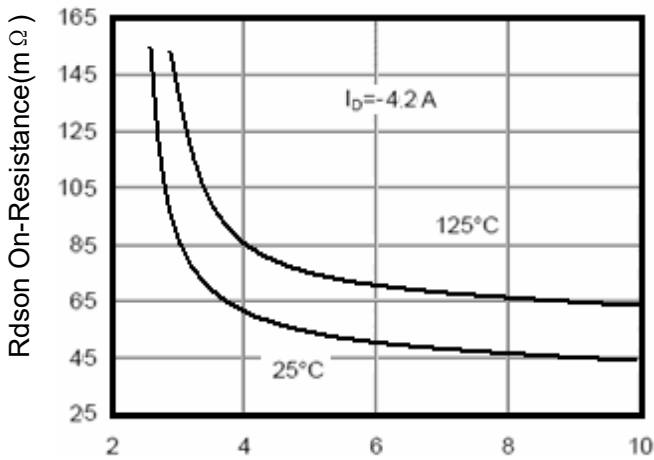
I_D- Drain Current (A)
Figure 4 Drain-Source On-Resistance



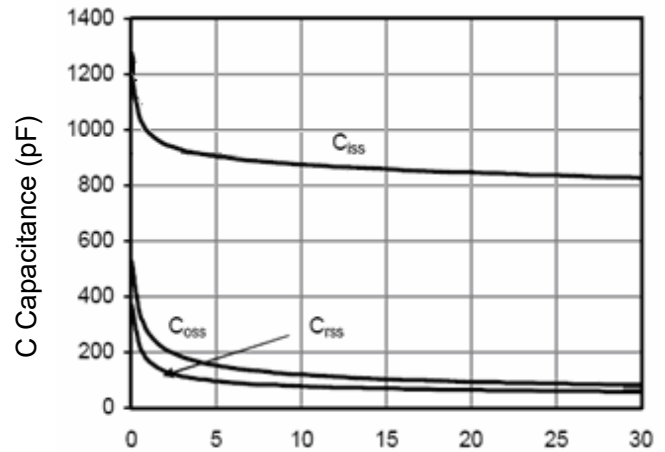
V_{gs} Gate-Source Voltage (V)
Figure 5 Transfer Characteristics



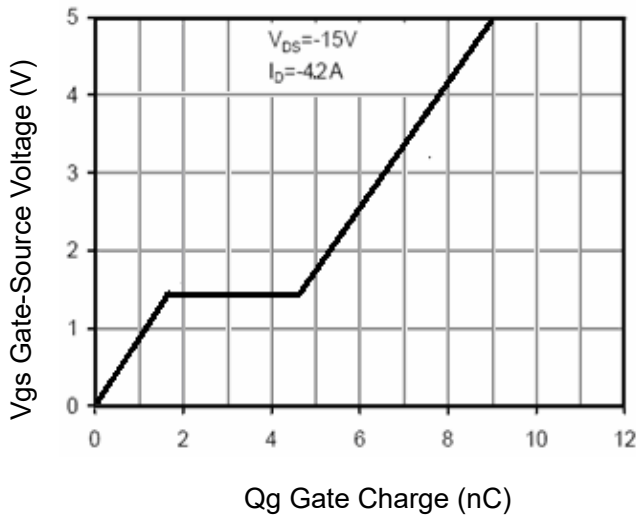
T_J-Junction Temperature(°C)
Figure 6 Drain-Source On-Resistance



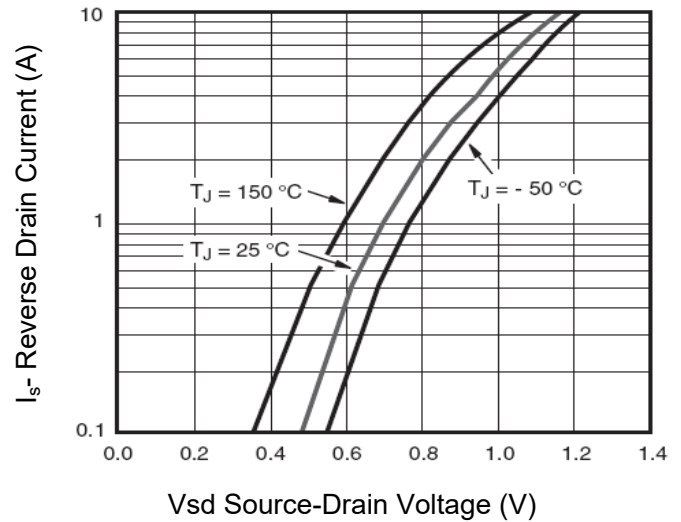
Vgs Gate-Source Voltage (V)
Figure 7 Rdson vs Vgs



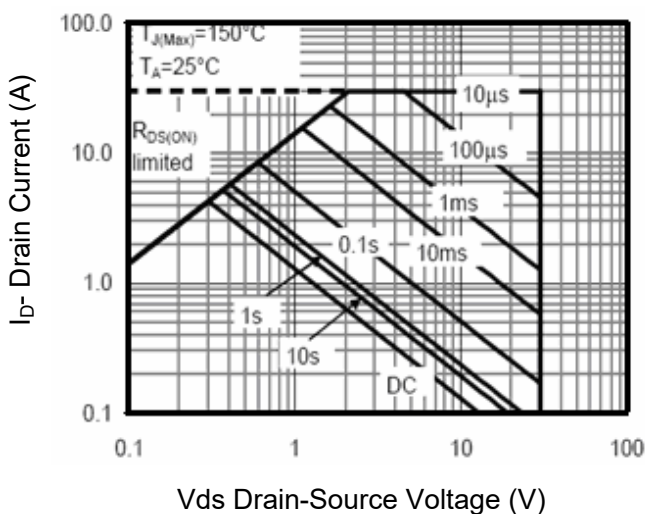
Vds Drain-Source Voltage (V)
Figure 8 Capacitance vs Vds



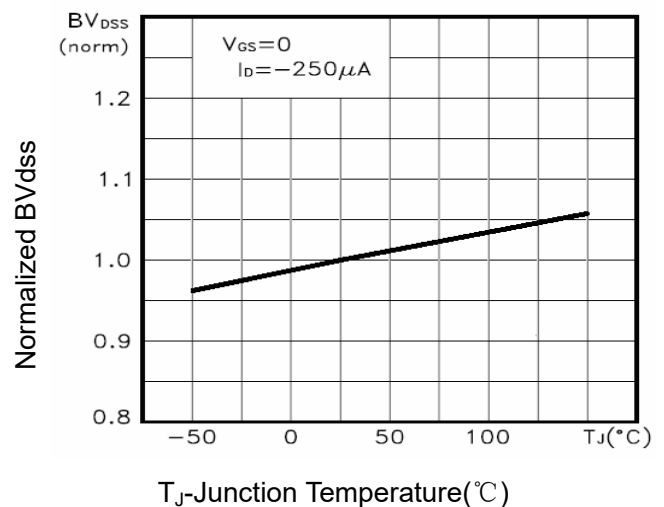
Qg Gate Charge (nC)
Figure 9 Gate Charge



Vsd Source-Drain Voltage (V)
Figure 10 Source-Drain Diode Forward



Vds Drain-Source Voltage (V)
Figure 11 Safe Operation Area



T_J-Junction Temperature(°C)
Figure 12 BV_{DSS} vs Junction Temperature

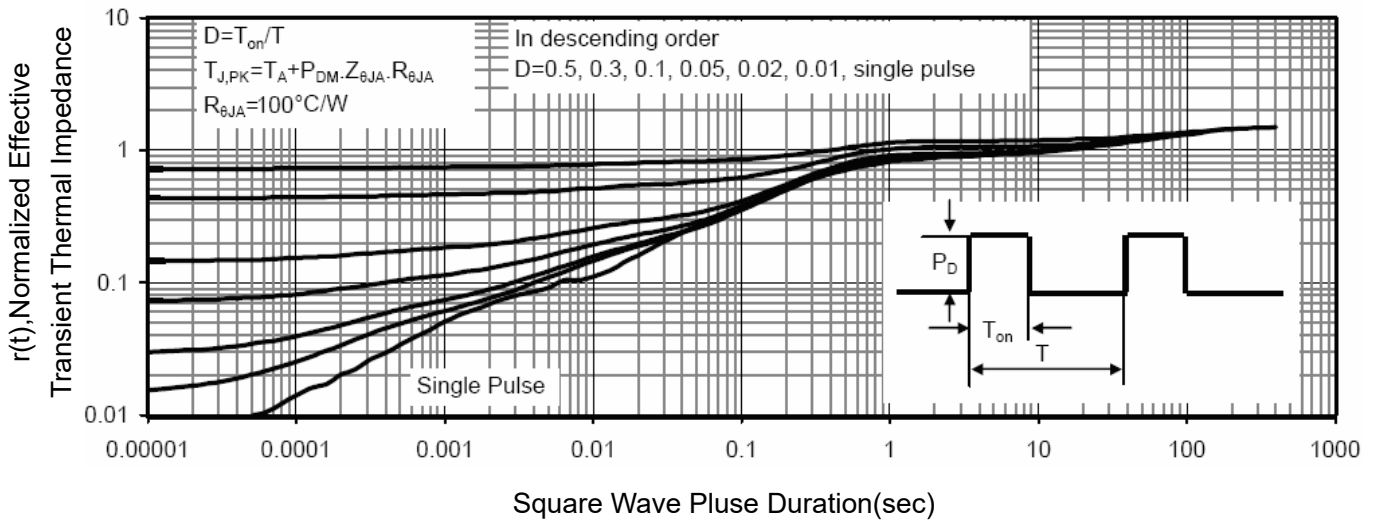
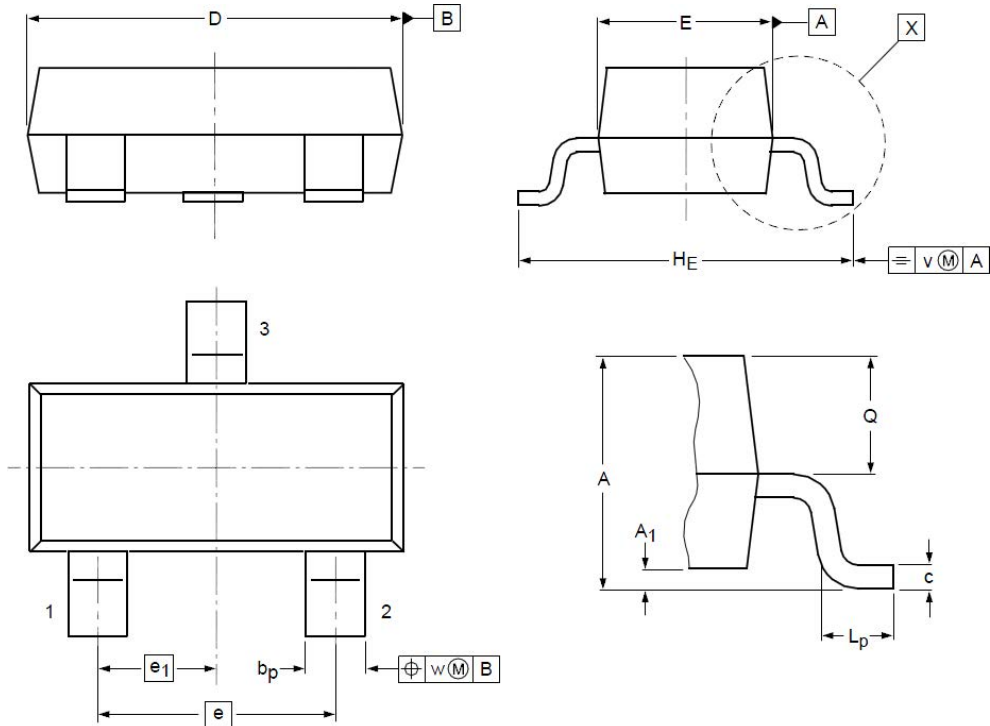


Figure 13 Normalized Maximum Transient Thermal Impedance

SOT23 Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	0.90	1.05	1.20	e₁	--	0.95	--
A₁	0.01	0.05	0.10	H_E	2.10	2.40	2.50
b_p	0.38	0.42	0.48	L_p	0.40	0.50	0.60
c	0.09	0.13	0.15	Q	0.45	0.49	0.55
D	2.80	2.92	3.00	V	--	0.20	--
E	1.20	1.33	1.40	W	--	0.10	--
e	--	1.90	--				